

In re: Kim et al.
Serial No.: 10/706,755
Filed: November 12, 2003
Page 2 of 13

In the Title:

Please replace the Title with the following amended Title:

INTEGRATED CIRCUIT STRUCTURES INCLUDING EPITAXIAL SILICON
LAYERS THAT EXTEND FROM AN ACTIVE REGION THROUGH AN INSULATION
LAYER TO A SUBSTRATE ~~IN ACTIVE REGIONS AND METHODS OF FORMING~~
SAME

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Page 3 of 13

In the Specification:

Please replace the paragraph beginning at page 6, line 8 with the following amended paragraph:

Referring to Fig. 5D, the sacrificial layer 12 exposed by the trench is removed, thereby forming a gap between the silicon layer 14 and the substrate 10. In particular, the gap exposes a bottom surface of the silicon layer 14, a side wall of the epitaxial layer 20 and a top surface of the substrate 10. The etching process used to remove the sacrificial layer 12 may use a dry etch by supplying plasma of one or more of the following gases: hydrogen (H₂), oxygen (O₂), nitrogen (N₂) and fluorine compounds such as NF₃ and CF₄, without applying a bias in a dry etch chamber. The etch process used to remove the sacrificial layer 12 may employ a wet etch using one or more of the following solutions: ammonia water (NH₄OH), hydrogen peroxide (H₂O₂), deionized water (H₂O), nitric acid (HNO₃) and fluorine acid (HF).